Valley blockade in a silicon double quantum dot

Justin K. Perron*
California State University San Marcos, Department of Physics, California 92096 and
Joint Quantum Institute, National Institute of Standards and Technology, Gaithersburg, Maryland 20899, USA

Michael J. Gullans and Jacob M. Taylor
Joint Quantum Institute, National Institute of Standards and Technology, Gaithersburg, Maryland 20899, USA and
Joint Center for Quantum Information and Computer Science,
University of Maryland, College Park, Maryland 20742, USA

M. D. Stewart, Jr. and Neil M. Zimmerman†
National Institute of Standards and Technology, Gaithersburg, Maryland 20899, USA
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Electrical transport in double quantum dots (DQDs) illuminates many interesting features of the dots' carrier states. Recent advances in silicon quantum information technologies have renewed interest in the valley states of electrons confined in silicon. Here we show measurements of DC transport through a mesa-etched silicon double quantum dot. Comparing bias triangles (i.e., regions of allowed current in DQDs) at positive and negative bias voltages we find a systematic asymmetry in the size of the bias triangles at the two bias polarities. Asymmetries of this nature are associated with blocking of tunneling events due to the occupation of a metastable state. Several features of our data lead us to conclude that the states involved are not simple spin states. Rather, we develop a model based on selective filling of valley states in the DQD that is consistent with all of the qualitative features of our data.

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The conduction band of indirect semiconductors have multiple degenerate minima. Silicon, for example, has six equivalent minima (or valleys) at wave vectors 85% of the way to the zone boundary in the equivalent [100] directions. This means conduction electrons have an additional degree of freedom when compared to those in direct gap semiconductors (with conduction band minima centered at $k = 0$). Although some implications of this valley degree of freedom were measured as far back as 1966 in Shubnikov-de Haas oscillations[1], there has been a recent spike in the amount of work focusing on the valley properties of conduction electrons in silicon. This includes measurements of valley splittings in different Si-based quantum dots[2–8]. Much of the impetus behind this interest is due to recent developments in solid state quantum computation. These developments have highlighted several ways in which the valley state of conduction electrons can influence the quantum behaviour of confined electrons. This includes the lifting the Pauli-spin blockade (PSB) that is often used for initialization and readout[9], valley induced oscillations of the exchange interaction over atomic length scales[10], and spin relaxation hot spots[5]. Valley states are also believed to influence the voltage induced g-factor shift of a quantum dot spin[11] which enables spin qubit addressability[12]. Furthermore, when creating an electron spin qubit one needs two isolated spin states; this requires the lowest lying valley states be separated by an energy larger than the Zeeman splitting of the spin states.

In this Letter, we report transport measurements of a silicon double quantum dot that reveal a rectification effect between bias voltage polarities. To explain our data we propose a model involving the valley degree of freedom and a substantial difference in the electron filling of the two quantum dots. This model suggests this type of blockade could be used to probe several aspects of valley physics similar to how PSB has been used to probe solid state spin physics.

Our device [see figure 1(a)] consists of a mesa-etched silicon nanowire formed from a (100) silicon-on-insulator substrate. A SiO_2 dielectric layer separates three polysilicon finger gates from the nanowire. These gates, spaced 40 nm edge-to-edge, conformally coat the nanowire and are used to electrostatically create conduction barriers. A second SiO_2 dielectric layer electrically isolates the finger gates from a polysilicon global upper gate which is used to turn on conduction in the device. Far from the active device area shown, ohmic contacts are formed on small degenerately doped regions of the mesa-etched silicon. In addition to forming the barriers between the quantum dots and the source drain leads, the outermost finger gates also serve as plunger gates, raising and lowering the chemical potentials of the quantum dots.

Figure 1b) shows DC transport measured in our device as a function of the voltages on the outer two finger gates, V_{LGD} and V_{LGS}. All data presented are taken in a dilution refrigerator at a nominal base temperature of 45 mK. The measurement results in a honeycomb stability diagram where each cell of the honeycomb corresponds to a constant number of electrons on each dot[13]. At the corners of each hexagonal cell are regions, called bias triangles, where a tunneling current is energetically favorable. Since the applied source-drain bias voltage V_b, determines the energy window between the Fermi levels

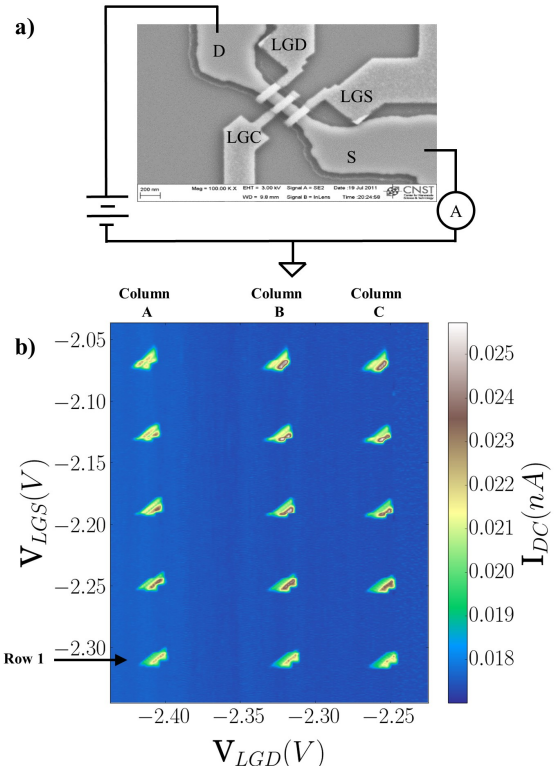

FIG. 1. **Charge Stability Diagram: a)** Scanning electron micrograph of a device similar to the one measured. Current is measured at the source lead with the bias voltage applied to the drain. Not shown is a global upper-gate used to turn on conduction in the silicon. **b)** DC transport through our double quantum dot measured with V_b = 1.5 mV, an upper gate voltage of $V_{\rm UG}$ = 3.5 V, and a center lower gate voltage of $V_{\rm LGC}$ = − 1.733 V. This measurement spans five charge transitions on the source side dot and three on the drain side dot. At lower $V_{\rm LGS}$ and $V_{\rm LGD}$ values the signal to noise ratio prevents measurement of bias triangles, while at higher values the bias triangles are not very well formed as cotunneling effects begin to become evident.

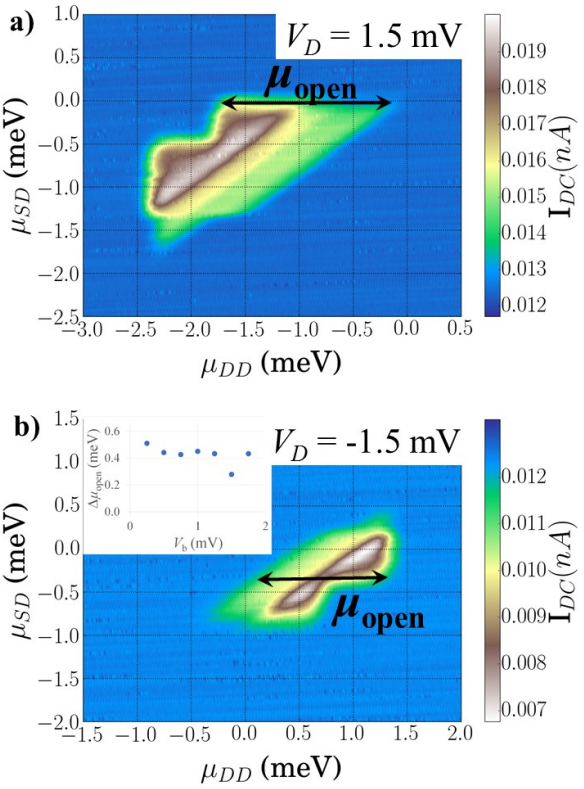

FIG. 2. **Size Asymmetry** More detailed data of the bias triangles from column B and row 2 in figure 1. **a)** Measured with V_b = 1.5 mV, **b)** measured with V_b = -1.5 mV. The size asymmetry of the triangles can be quantified by $\Delta\mu_{\rm open}$ which is calculated using the $\mu_{\rm open}$ values indicated by the black arrows. The size difference is independent of the magnitude of V_b as shown in the inset. Similar asymmetries were observed on the majority of charge transitions pictured in figure 1.

of the two leads, one expects the size of the bias triangles to be proportional to $|V_b|$[13], and that the polarity of the bias should not change the size of the triangles. When comparing bias triangle sizes it is convenient to convert the data from a voltage space picture to a chemical potential space picture[14] where data is plotted as a function of the chemical potentials of the drain and source dots, $\mu_{\rm DD}$ and $\mu_{\rm SD}$. The conversion involves the various lever arms of the applied voltages and allows the data to be displayed on axes with units of energy. Figure 2 show measurements made at V_b = 1.5 mV and -1.5 mV plotted this way. These plots contradict the expectation that bias triangle size should not change with polarity of source-drain bias in the large electron number limit; they clearly show a substantial difference in the size between triangles measured with opposite polarities.

We quantify the size of each bias triangle in terms of $\mu_{\rm open}$, defined as the length of the bias triangle side parallel to the $\mu_{\rm DD}$ axis. Experimentally the end points of the side are determined using a contour plotted at a current level just above the noise floor. The size asymmetry can then be quantified by

$$\Delta\mu_{\rm open} = \mu_{\rm open}\,|_{V_b=1.5\ \rm mV} - \mu_{\rm open}\,|_{V_b=-1.5\ \rm mV}\,. \quad (1)$$

As shown in the inset of figure 2 this size difference is independent of $|V_b|$.

Size asymmetries of this nature are typically associated with current rectification due to a metastable excited state of the electrons on the DQD. The most common example is PSB[15–25], where the occupation of a spin triplet state in the (1,1) charge configuration prevents current flow that would otherwise be allowed through the ground singlet states[26].

Comparisons between our data and qualitative expectations of PSB reveals several inconsistent features. First, the size asymmetry of figure 2 exists at nearly all the transitions shown in figure 1 whereas PSB, generi-

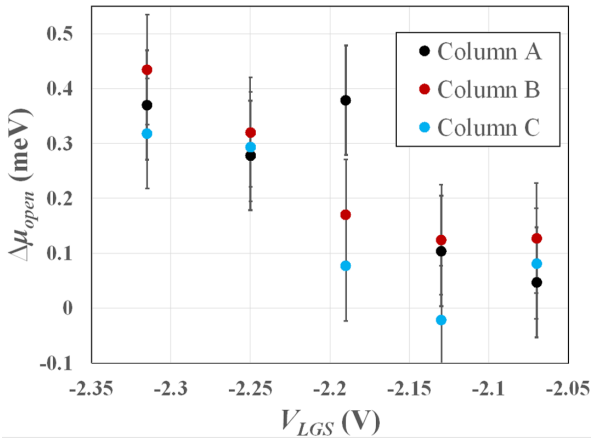

FIG. 3. **Gate dependence** Dependence of $\Delta\mu_{\text{open}}$ on V_{LGS}. There is a general trend of decreasing $\Delta\mu_{\text{open}}$ as the source dot is successively filled. This trend comes about naturally in the valley band model (see text).

cally being an odd-even filling effect, is expected in, at most, 1/2 of the transitions[27] . Second, all of the asymmetries observed had the same polarity (larger triangles measured with $V_b > 0$). In contrast, PSB is expected to show size asymmetries with alternating polarity as one moves through the honeycomb[16]. Third, our data also does not have a systematic trend with respect to magnetic field B_0 applied perpendicular to the substrate (see supplemental info), whereas with PSB, one expects a systematic change in the size of the bias triangles. This change is expected because the exchange energy can have a magnetic field dependence[16], and the energy of the polarized spin triplet states have a magnetic field dependence due to the Zeeman effect[14, 17]. Fourth, as shown in figure 3, our data show a systematic dependence on V_{LGS} that is unexpected for the case of PSB. Although changing the voltage applied to a barrier gate can change the magnitude of the exchange energy[20], the effect is too small to be a plausible explanation for the trend we observe.

The inconsistencies between our data and traditional PSB lead us to believe the asymmetries in our bias triangles are not due to spin states; therefore, another degree of freedom must be responsible for the rectification. We developed a model of blockade that centers on the valley degree of freedom of electrons in silicon. In our model, we assume all the conduction electrons in the DQD occupy one of two valley states, v_+ and v_-. However, the relative large size and electron occupation of our dots results in bands of states for each valley type. The bottom of the bands of each type are separated by the valley splitting Δ_v, which depends primarily on the surface potential experienced by the electrons[28]. The splittings between successive levels in the individual bands are predominantly determined by the orbital spacing E_{orb}.

Figure 4 shows the details of this model in the simplified constant interaction picture where we have suppressed the charging energy to evoke the idea of bands, appropriate near the triple points of the honeycomb. In the limit of empty dots the ground state chemical potential is the same for both dots. This situation results in typical bias triangles with no asymmetry. However, by adding electrons to one of the two dots we can fill the lower lying valley state band up to an energy greater than Δ_v. This filling makes the chemical potentials of the two valley types degenerate for that dot. Since the potentials are still split on the other dot a situation arises where an electron loads into a v_- state only to become trapped since the interdot tunneling event is energetically unfavorable for v_- states. Thus, current is blocked until some valley relaxation or inter-valley tunneling event occurs[29]. As with PSB, this blockade results in a bias triangle size asymmetry $\Delta\mu_{\text{open}}$, that corresponds to the splitting of the chemical potentials on the blocking dot. In our valley blockade model this splitting can be reduced by adding electrons to the blocking dot and successively filling the lower energy valley band.

The blockade predicted by this model is in qualitative agreement with our data. It predicts 1) blockade for multiple successive charge transitions 2) all with the same polarity of size asymmetry, 3) the magnetic field dependence of the bias triangle size would depend heavily on the details of the levels that make up the bands, but is by no means expected to be monotonic or even systematic. Finally, 4) a reduction in $\Delta\mu_{\text{open}}$ as a function of dot occupation as observed in the data of figure 3.

For the model to apply several things must be true. First and most crucially, there must be low inter-valley tunneling rates. Furthermore, the z orbital spacing E_z, where z is the direction perpendicular to the substrate, must be large relative to both Δ_v and the lateral orbital spacing E_{lat}. If this were not the case, adding electrons to one of the dots would cause significant changes to the z-dependence of the wave function, which would distort the relative valley states on each dot, leading to inter-valley tunneling. In addition to the restriction on E_z, the lateral orbital spacing must be small relative to Δ_v for the band-like picture to be accurate. Using a constant interaction picture and applying this model to our data we can extract certain energies. The largest splitting in figure 3 of 0.4 meV gives a lower bound on Δ_v. This value is in the range of 0.1 meV to 0.8 meV reported by references [5] and [30]. The slope of figure 3 implies a lateral orbital splitting $E_{\text{lat}} \sim 0.1$ meV. Furthermore, with a noise level in our experiment of ± 0.1 pA, this model gives a valley lifetime of $T_{1,v} \geq 1$ μs.

The model we have described, although consistent with our data, should be verified with future measurements. Devices with extended functionality will allow for more quantitative comparisons between the model and experiment. Specifically, independent plunger gates for each of the dots as well as an ancillary dot for charge sens-

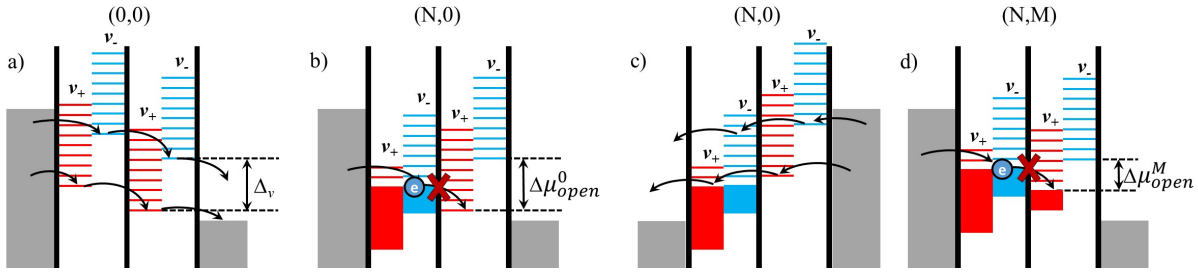

FIG. 4. **Model:** Our model in the simplified constant interaction picture. We have suppressed the charging energy to evoke the idea of bands. **a)** Red and blue levels correspond to v_+ and v_- valley types respectively. When the dots are empty $(0,0)$, the ground states in each dot are the same valley type, and the splitting to the lowest state in the opposite valley is also equal. This results in no blockade, and bias triangles with size determined by $|V_b|$. **b)** Filling the first dot with N electrons, enough to fill all the v_+ states below the ground v_- state removes the splitting between the chemical potentials of the two valley types. Blockade will occur when these degenerate levels lie between the ground v_+ and v_- states on the second dot, resulting in a bias triangle size asymmetry of Δ^0_{open}. **c)** Reversing the bias polarity in this situation results in fully formed bias triangles with no blockade. Whenever the interdot tunneling is favorable for the lower v_+ states the same is true for the v_- states. **d)** Adding M electrons to the second dot reduces the size asymmetry to $\Delta\mu^M_{\text{open}}$ by filling v_+ states and brining the v_+ chemical potential closer to that of v_-.

ing would allow for the exact electron fillings to be determined. Charge sensing would also allow for a much wider range of state lifetimes to be probed. In addition to verifying our model, this would open the door to investigations of the coupling and relaxation mechanisms[31].

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* jperron@csusm.edu
† Neil.Zimmerman@nist.gov, Tel: (301) 975-5887

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Supplemental information for Valley blockade in a silicon double quantum dot

Justin K. Perron*
California State University San Marcos, Department of Physics, California 92096 and
Joint Quantum Institute, National Institute of Standards and Technology, Gaithersburg, Maryland 20899, USA

Michael J. Gullans and Jacob M. Taylor
Joint Quantum Institute, National Institute of Standards and Technology, Gaithersburg, Maryland 20899, USA and
Joint Center for Quantum Information and Computer Science,
University of Maryland, College Park, Maryland 20742, USA

M. D. Stewart, Jr. and Neil M. Zimmerman†
National Institute of Standards and Technology, Gaithersburg, Maryland 20899, USA
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* jperron@csusm.edu
† Neil.Zimmerman@nist.gov, Tel: (301) 975-5887

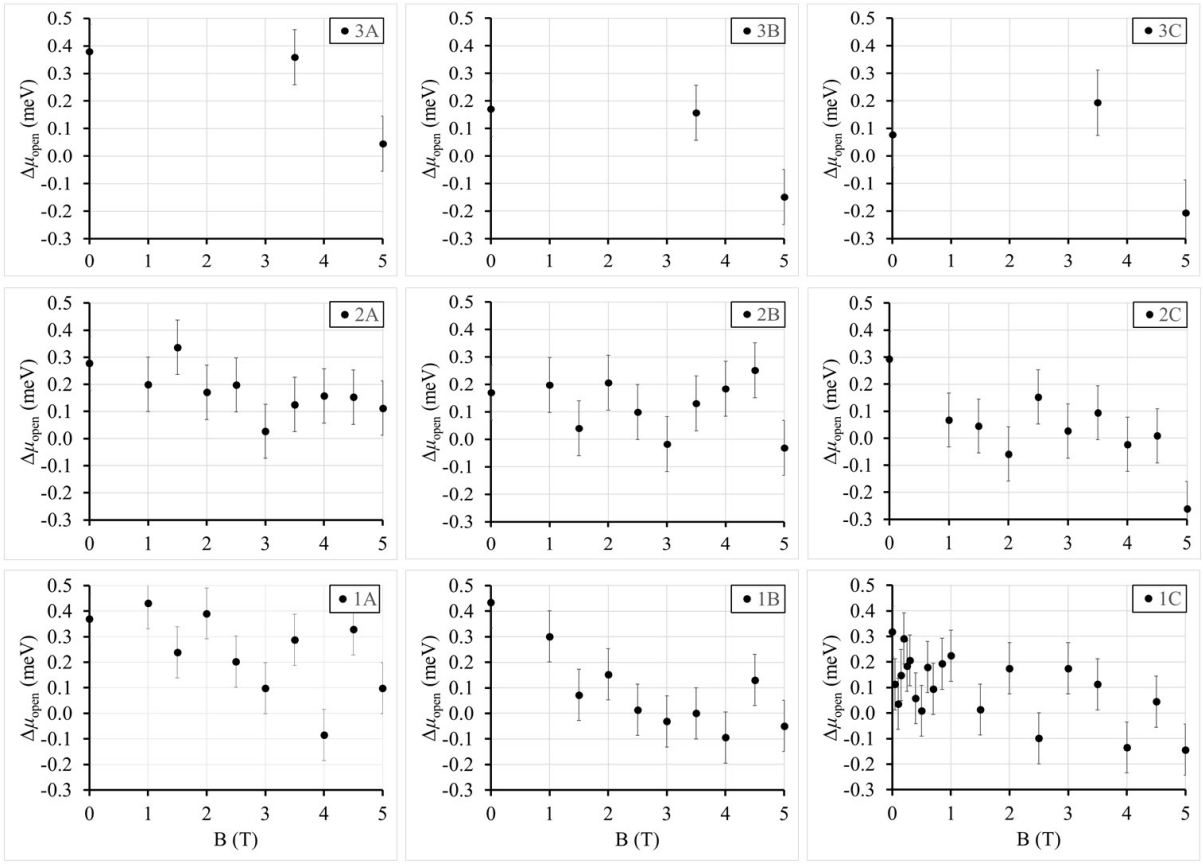

FIG. S1. **Perpendicular Magnetic field dependence** $\Delta\mu_{open}$ as a function of the absolute value of the applied magnetic field perpendicular to the substrate. Transitions are labeled by row number and column letter as indicated in figure 1 of the main text. Although $\Delta\mu_{open}$ does change with magnetic field, the dependence is not what is expected from simple spin arguments.

In the main text we reference the size asymmetry quantified with $\Delta\mu_{open}$ as a function of magnetic field perpendicular to the substrate. Figure S1 shows all the data of $\Delta\mu_{open}$ as a function of magnetic field. Although the magnetic field does change the magnitude of the size asymmetry, the dependence is not as systematic as one would expect from simple spin states. For simple spin states Zeeman effects on the spin energies as well as magnetic field effects on the exchange energy J are expected to change $\Delta\mu_{open}$. In both cases one expects a monotonic dependence not observed in our data[1, 2]. However, the valley blockade model introduced in this paper involves many electron states, and could be expected to have a much more complicated magnetic field dependence. Calculation of the dependencies is beyond the scope of this paper, however, we feel this data supports our belief that the states causing the current rectification in our data are not simple spin states.

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